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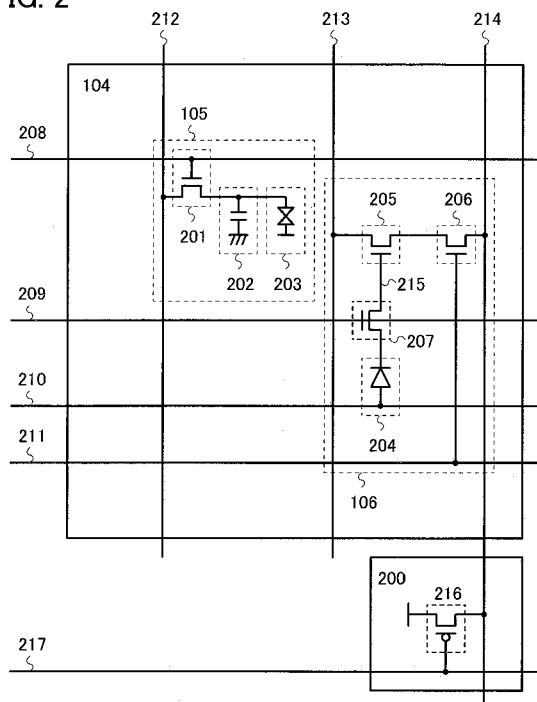
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(54) Title: SEMICONDUCTOR DEVICE AND METHOD FOR DRIVING THE SAME

FIG. 2



(57) Abstract: A semiconductor device includes a photodiode, a first transistor, and a second transistor. The photodiode has a function of supplying a charge corresponding to incident light to a gate of the first transistor, the first transistor has a function of accumulating the charge supplied to the gate, and the second transistor has a function of retaining the charge accumulated in the gate of the first transistor. The second transistor includes an oxide semiconductor.

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